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**ABSTRACT**

A substrate liquid processing method includes preparing a substrate having a recess on a surface thereof, a seed layer being formed on a surface of the recess; bringing a first pretreatment liquid, containing a reducing agent, a pH adjuster, and an additive configured to accelerate or inhibit an electroless plating reaction, into contact with the seed layer; and precipitating, after the bringing of the first pretreatment liquid into contact with the seed layer, a plating metal in the recess by supplying a first electroless plating liquid to the recess.

